

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	71842	(thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:09
L2	135420	(memory near cells)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:10
L3	1495420	(electrode\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:10
L4	10161	(electrode\$1) with (voltage) with (temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:33
L5	6	1 and 2 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:33
L6	311229	(electrode\$1) with (voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:33
L7	119	1 and 2 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:33
L8	0	7 and (electrode near15 thrysistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:33
L9	15	7 and (electrode near15 thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:34

L10	15	9 and (electrode with voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:34
L11	7	10 and (voltage near15 thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:00
L12	7	10 and (voltage with thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:00
L13	6	12 and (electrode near10 voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:16
L14	2	12 and (electrode near10 voltage near10 thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:04
L15	1632	(electrode near10 voltage near10 thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:06
L16	0	15 and (memory near cell) near15 (thyrisitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:04
L17	0	15 and (memory near3 cell) near15 (thyrisitor\$1).	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:05
L18	0	15 and (cell) near15 (thyrisitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:05
L19	0	15 and (memory) near15 (thyrisitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:05

L20	2	15 and (memory near3 cell) near15 (thyristor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:05
L21	2	15 and (memory near3 cell) with (thyristor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:06
L22	2	15 and (memory near3 cell) same (thyristor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:06
L23	3	15 and (memory near3 cell) and (thyristor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:06
L24	3	15 and (memory near3 cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:06
L25	105	(electrode) with (voltage near7 bias) with (thyristor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:07
L26	0	25 and (memory near cell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:07
L27	8	25 and (memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:07